Amendments to the Specification:

Please amend paragraphs **[06] - [10]** as follows:

Delete paragraphs 06, 07, 09 and amend paragraphs 08 and 10.

~~[06] One embodiment of the invention is directed to a semiconductor device comprising: a) a semiconductor substrate; b) a first region of a first conductivity type in the semiconductor substrate; c) a second region of a second conductivity type in the semiconductor substrate; d) a plurality of charge control electrodes, wherein each charge control electrode in the plurality of charge control electrodes is adapted to be biased differently than other charge control electrodes in the plurality of charge control electrodes; and e) a dielectric material disposed around each of the stacked charge control electrodes.~~

~~[07] Another embodiment of the invention is directed to a field effect transistor comprising: a) a semiconductor substrate of a first conductivity type having a major surface, a drift region, and a drain region; b) a well region of a second conductivity type formed in the semiconductor substrate; c) a source region of the first conductivity type formed in the well region; d) a gate electrode formed adjacent to the source region; e) a plurality of stacked charge control electrodes buried within the drift region, wherein each charge control electrode of the plurality of stacked charge control electrodes is adapted to be biased differently than another charge control electrode in the plurality of charge control electrodes, wherein the plurality of stacked charge control electrodes is adapted to adjust an electrical field profile within the drift region of the semiconductor substrate; and f) dielectric material disposed around each of the stacked charge control electrodes.~~

[08] Another embodiment of the invention is directed to a method for forming a semiconductor device, the method comprising: ~~a)~~ providing a semiconductor substrate having a first region of a first conductivity type; ~~b)~~ forming a region of a second conductivity type in the semiconductor substrate such that the first and second regions form a p-n junction; and~~; c)~~ forming **[[a]]** first and second charge control ~~electrode; and d) forming a second charge control~~

~~electrode~~ electrodes adjacent to but insulated from one of the first and second regions, along a dimension parallel to flow of current through the semiconductor device, wherein the first charge control electrode is adapted to be biased differently than the ~~first~~ second charge control electrode.

~~[09] Another embodiment of the invention is directed to a field effect transistor comprising: a) a semiconductor substrate of a first conductivity type having a major surface, a drift region, and a drain region; b) a well region of a second conductivity type formed in the semiconductor substrate; c) a source region of the first conductivity type formed in the well region; d) a source contact layer coupled to the source region; e) a gate electrode formed adjacent to the source region; f) a charge control electrode buried within the drift region, wherein the charge control electrode is adapted to be biased at a different potential than the gate electrode or the source contact layer, and is adapted to control the electric field in the drift region; and g) a dielectric material disposed around the charge control electrode.~~

[10] Another embodiment of the invention is directed to a method for forming a field effect transistor comprising: a) providing a semiconductor substrate of a first conductivity type having a major surface, a drift region, and a drain region; b) forming a well region of a second conductivity type in the semiconductor substrate; c) forming a source region of the first conductivity type in the well region; d) forming a source contact layer on the source region; e) forming a gate electrode adjacent to the source region; f) forming a charge control electrode ~~within~~ in the drift region, wherein the charge control electrode is adapted to be biased at a different potential than the gate electrode or the source contact layer, and is adapted to control the electric field in the drift region; and g) forming a dielectric material around the charge control electrode.